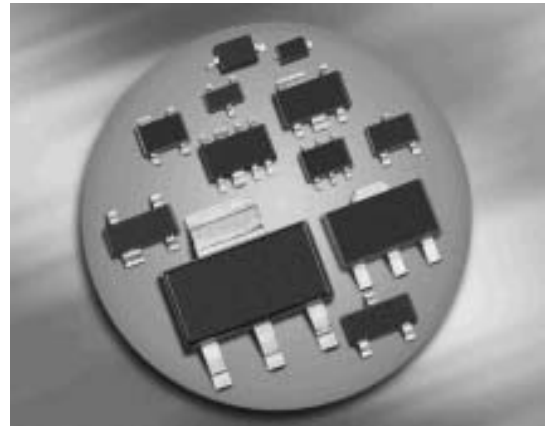


Silicon Variable Capacitance Diode

- For tuning of extended frequency band in VHF TV / VTR tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



BB639C
BB659C/-02V



Type	Package	Configuration	L_S (nH)	Marking
BB639C	SOD323	single	1.8	yellow S
BB659C	SCD80	single	0.6	HH
BB659C-02V	SC79	single	0.6	H

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \geq 5\text{k}\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

¹Pb-containing package may be available upon special request

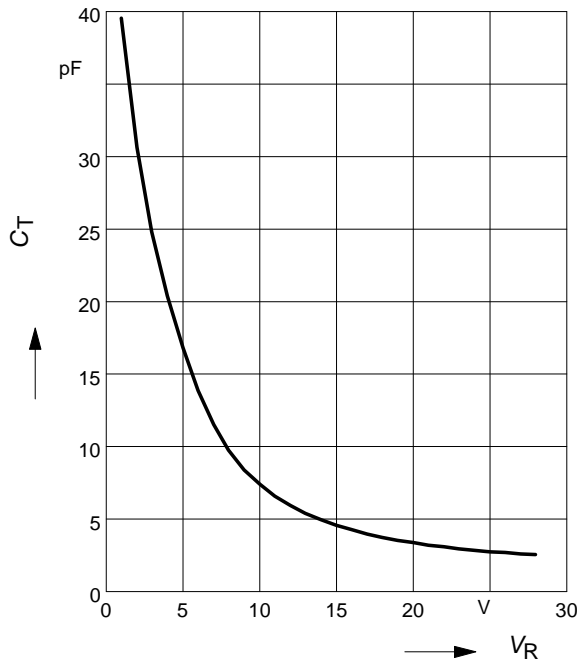
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				nA
$V_R = 30\text{ V}$		-	-	10	
$V_R = 30\text{ V}, T_A = 85^\circ\text{C}$		-	-	200	
AC Characteristics					
Diode capacitance	C_T				pF
$V_R = 1\text{ V}, f = 1\text{ MHz}$		36.5	39	42	
$V_R = 2\text{ V}, f = 1\text{ MHz}$		27	30.2	33.2	
$V_R = 25\text{ V}, f = 1\text{ MHz}$		2.5	2.72	3.05	
$V_R = 28\text{ V}, f = 1\text{ MHz}$		2.4	2.55	2.75	
Capacitance ratio	C_{T1}/C_{T28}	14.2	15.3	-	
$V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$					
Capacitance ratio	C_{T2}/C_{T25}	9.5	11.1	-	
$V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_T/C_T$				%
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence},$ BB639C		-	-	2.5	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 4\text{ diodes sequence},$ BB659C/-02V		-	0.3	1	
$V_R = 1\text{V to } 28\text{V}, f = 1\text{ MHz}, 7\text{ diodes sequence},$ BB659C/-02V		-	0.5	2	
Series resistance	r_S	-	0.6	0.7	Ω
$V_R = 5\text{ V}, f = 470\text{ MHz}$					

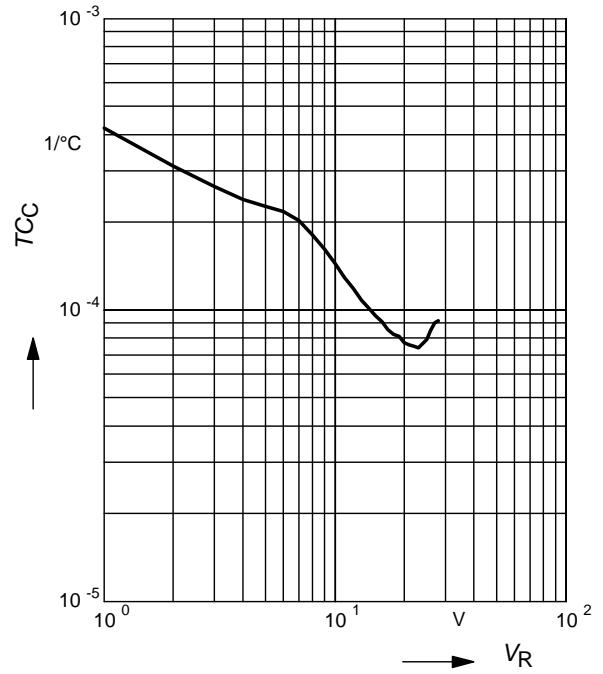
¹For details please refer to Application Note 047

Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

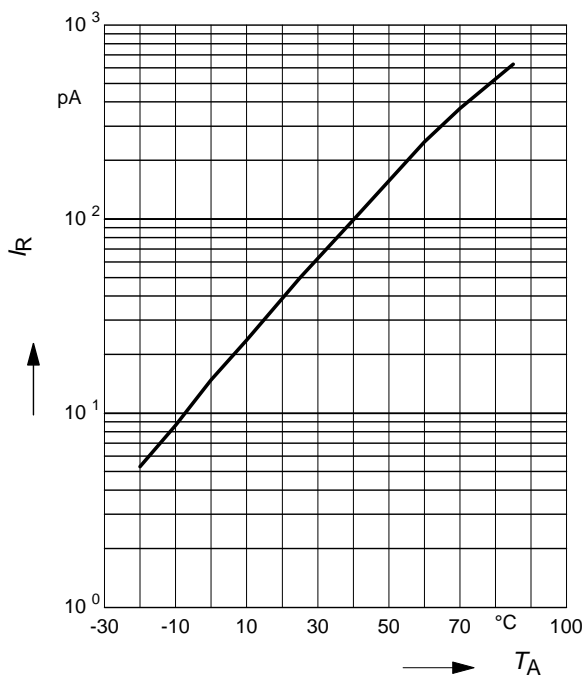


Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$



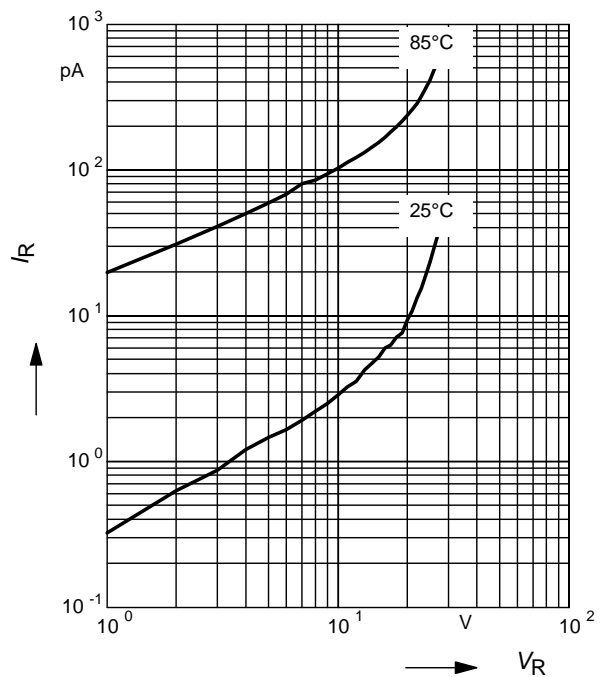
Reverse current $I_R = f(T_A)$

$V_R = 28\text{V}$

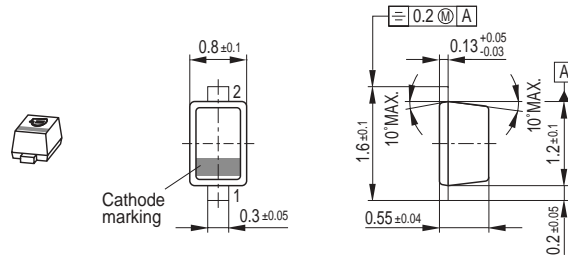


Reverse current $I_R = f(V_R)$

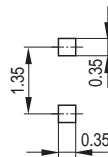
$T_A = \text{Parameter}$



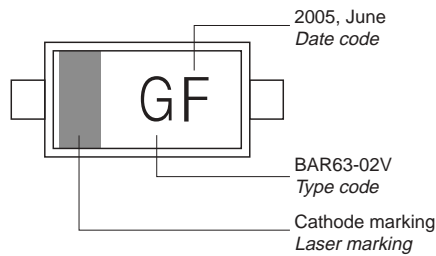
Package Outline



Foot Print

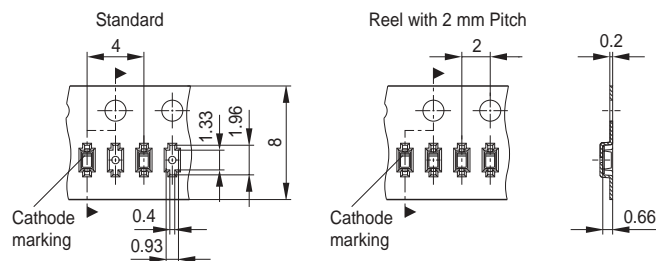


Marking Layout (Example)

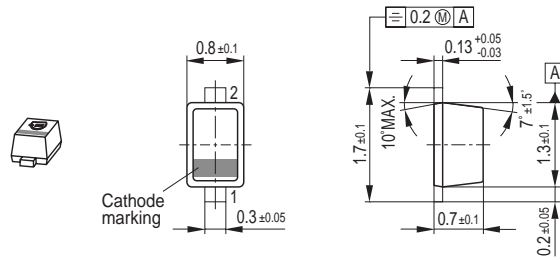


Standard Packing

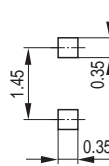
Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 180 mm = 8.000 Pieces/Reel (2 mm Pitch)
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



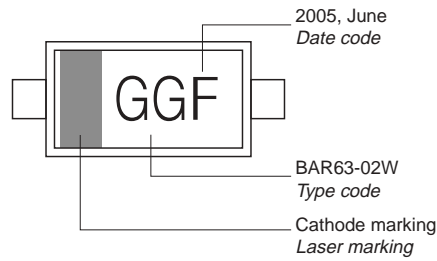
Package Outline



Foot Print

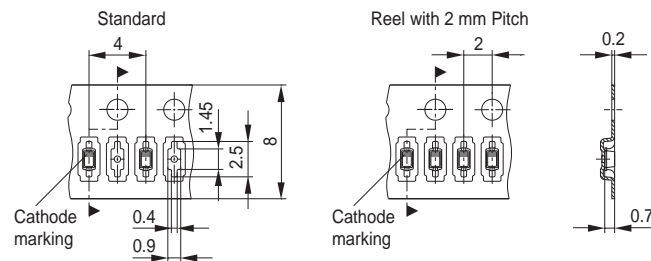


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 180 mm = 8.000 Pieces/Reel (2 mm Pitch)
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

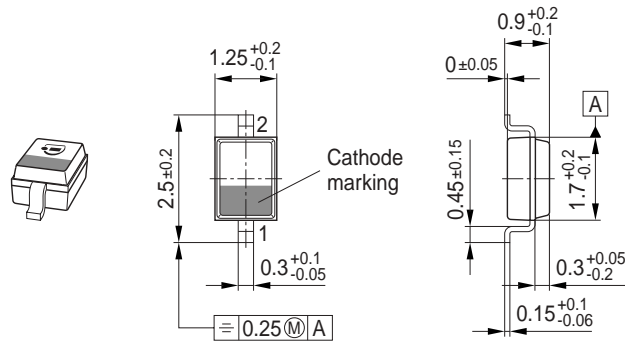


Date Code marking for discrete packages with
one digit (SCD80, SC79, SC75¹⁾) CES-Code

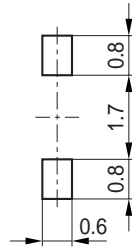
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

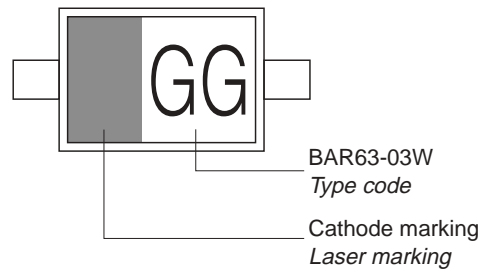
Package Outline



Foot Print

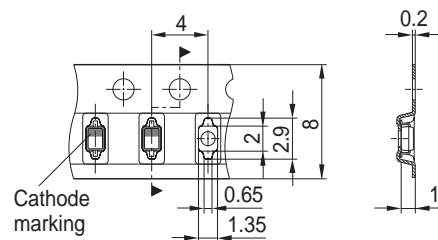


Marking Layout (Example)



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
Reel $\varnothing 330$ mm = 10.000 Pieces/Reel



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